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# B.M.S. College of Engineering, Bengaluru-560019

Autonomous Institute Affiliated to VTU

## May 2023 Semester End Make-Up Examinations

**Programme: B.E.**

**Semester: V**

**Branch: Electronics and Communication Engineering**

**Duration: 3 hrs.**

**Course Code: 16EC5DCMWE**

**Max Marks: 100**

**Course: Microwave Engineering**

**Date: 17.05.2023**

**Instructions:** 1. Answer any FIVE full questions, choosing one full question from each unit.  
2. Missing data, if any, may be suitably assumed.

### UNIT - I

1 a) Why transmission lines are called distributed parameter networks? Derive the expression for voltage  $V(z)$  and current  $I(z)$  on a uniform transmission line considering lumped equivalent circuit of a small section of a uniform transmission line. **10**

b) Explain in brief reflection coefficient, Transmission coefficient and Standing wave ratio with respect to a transmission line. Derive the relation between them. **10**

### UNIT - II

2 a) State and prove properties of scattering matrix. **12**

b) S-parameters of a two-port network are given by **08**

$$[S] = \begin{bmatrix} 0.1\angle 0^\circ & 0.9\angle 45^\circ \\ 0.9\angle 45^\circ & 0.3\angle 45^\circ \end{bmatrix}$$

Determine whether network is (i) Reciprocal (ii) Lossless

What is the return loss at port 1 when port 2 is short circuited.

### UNIT - III

3 a) Explain construction and operation of a Magic-Tee with neat diagram. Obtain it's S-matrix. Explain any one application of Magic-Tee. **10**

b) A 3-port circulator has an insertion loss of 1dB and an isolation of 30dB. If VSWR=1.5, Obtain it's S-matrix. **10**

### OR

4 a) What is a circulator? Explain any one way of obtaining a 4-port circulator. Write it's S-matrix. **10**

b) Show that if a pair of ports of a 4-port lossless reciprocal Junction are de-coupled, the other pair of ports are also de-coupled. **10**

## UNIT - IV

5 a) Explain the construction and operation of PIN diode. Compare PIN diode with ordinary PN junction diode. With neat diagram, explain how a PIN diode is used as RF Switch. **10**

b) With neat diagrams, describe the construction of any one form of IMPATT diode. Explain its operation with relevant waveforms. **08**

c) An IMPATT diode has a drift length of 2 micro meter. Determine the operating frequency of IMPATT diode if the drift velocity for Si is  $10^7$  cm/sec. **02**

## OR

6 a) With neat diagrams, explain the working of Reflex Klystron Oscillator. A Reflex Klystron is to be operated at 10GHz with a beam voltage of 300V, Repeller space of 0.1 cm, and  $1\frac{3}{4}$  mode. Calculate PRF<sub>max</sub> and corresponding repeller voltage for a beam current of 20 mA. **12**

b) With neat diagram explain the working of a negative resistance Parametric Amplifier. Compare negative resistance Parametric amplifier and Parametric Up-converter. **08**

## UNIT - V

7 a) Explain what you understand by EMI and EMC and why it is important in RF design. **10**

b) Describe how microwaves are utilized in medical field and explain the effect of Microwaves on human body. **10**

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